

EAST - [10635790.wsp:1]

File View Edit Tools Window Help

☐ Drafts  
☐ Pending  
☒ Active  
     L1: (66) camouflag\$3 and reverse near engineer\$3  
     L2: (5) camouflag\$3 and reverse near engineer\$3 and silicide  
     L3: (16) reverse near engineer\$3 and silicide  
     L4: (2059) reverse near engineer\$3  
     L5: (474) reverse near engineer\$3 and semiconductor  
     L6: (242) reverse near engineer\$3 and semiconductor and channel  
     L7: (10) reverse near engineer\$3 and semiconductor and (channel with (conductivity))  
☐ Failed  
     reverse near engineer\$3 and semiconductor and (channel with (same near conductivity))  
     reverse near engineer\$3 and semiconductor and (channel with (same near conductivity))  
☐ Saved  
☐ Favorites  
☐ Tagged (0)  
☐ UDC  
☐ Queue  
☐ Trash

☒ DBs US-PG ☐ Plurals

Default operator: ☒ Highlight all hit terms initially

reverse near engineer\$3 and silicide

☒ BRS form ☒ IS&R form ☐ Image ☐ Text

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20020096776 A1	20020725	9	Integrated circuits protected against reverse engineering and method for	257/774	257/369; 438/199
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20020079564 A1	20020627	8	Anti-decphering contacts	257/679	257/922; 257/E21.575;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20010041431 A1	20011115	6	Semiconductor device with transparent link area for silicide applications and fabrication	438/527	257/E21.165; 257/E21.507;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6528885 B2	20030304	10	Anti-decphering contacts	257/758	257/750; 257/E21.575;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6410413 B1	20020625	6	Semiconductor device with transparent link area for silicide applications and fabrication	438/601	257/608; 257/E21.165;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6326675 B1	20011204	8	Semiconductor device with transparent link area for silicide applications and fabrication	257/608	257/E21.165; 257/E21.507
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6117762 A	20000912	8	Method and apparatus using silicide layer for protecting integrated circuits from	438/618	257/E21.165; 257/E21.59;
13	<input type="checkbox"/>	<input type="checkbox"/>	US 5882998 A	19990316	14	Low power programmable fuse structures and methods for making the same	438/601	257/209; 257/529;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5854510 A	19981229	14	Low power programmable fuse structures	257/529	257/208; 257/209;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5841787 A	19981124	14	Memory programming and test circuitry and methods for implementing the same	714/718	
16	<input type="checkbox"/>	<input type="checkbox"/>	US 5278105 A	19940111	11	Semiconductor device with dummy features in active layers	438/129	257/922; 257/E21.036;